BL Galaxy Electrical

Silicon Epitaxial Planar Transistor

SS8550

FEATURES

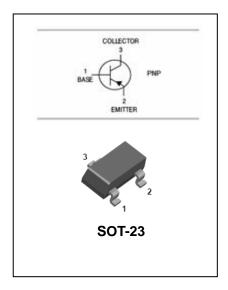
Collector Current.(I_C= 1.5A)



- Complementary To SS8550.
- Collector Dissipation: P_C=0.3W (T_C=25°C)

APPLICATIONS

High Collector Current.



ORDERING INFORMATION

Type No.	Marking	Package Code	
SS8550	Y2	SOT-23	

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-1.5	А
Pc	Collector Dissipation	0.3	W
T_{j},T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}$

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ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA,I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-0.1mA,I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V,I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-20V,I _B =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-0.1	μA
DC aument rain	h _{FE}	V _{CE} =-1V,I _C =-100mA	120		400	
DC current gain		V _{CE} =-1V,I _C =-800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B = -80mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B = -80mA			-1.2	V
Transition frequency	f⊤	V_{CE} =-10V, I_{C} = -50mA f=30MHz	100			MHz
Output capacitance	C _{ob}	V _{CB} =-10V,I _E =0,f=1MHz			20	pF
Base-emitter voltage	V_{BEF}	I _E =-1.5A			-1.6	V

CLASSIFICATION OF $h_{\text{FE}(1)}$

Rank	L	н	J
Range	120-200	200-350	300-400

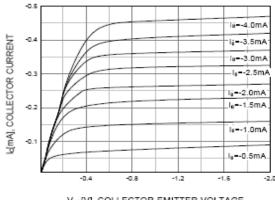
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TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Vot[V], COLLECTOR-EMITTER VOLTAGE

Figure 1. Static Characteristic

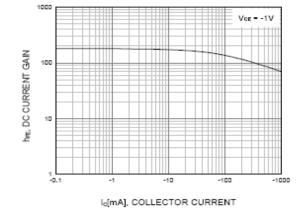


Figure 2. DC current Gain

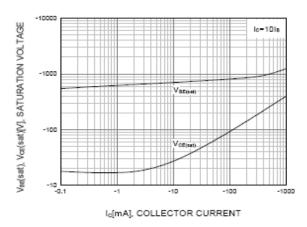


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

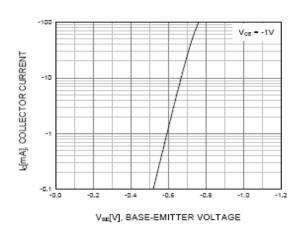


Figure 4. Base-Emitter On Voltage

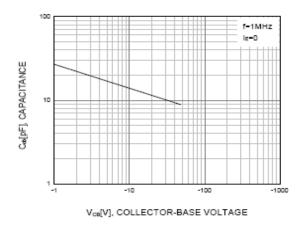


Figure 5. Collector Output Capacitance

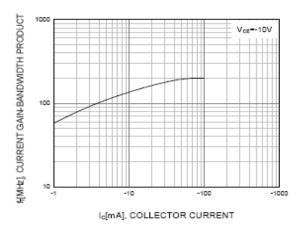


Figure 6. Current Gain Bandwidth Product

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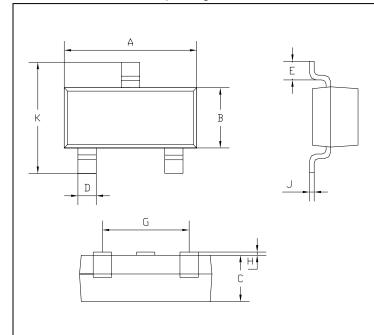
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PACKAGE OUTLINE

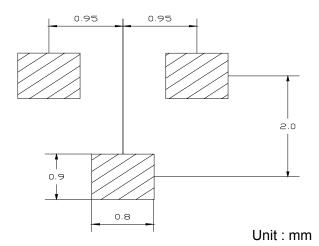
Plastic surface mounted package

SOT-23



SOT-23			
Dim	Min Max		
Α	2.85	2.95	
В	1.25	1.35	
С	1.0Typical		
D	0.37	0.43	
E	0.35	0.48	
G	1.85	1.95	
Н	0.02	0.1	
J	0.1Typical		
K	2.35	2.45	
All Dimensions in mm			

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
SS8550	SOT-23	3000/Tape&Reel